

10th International Conference on Radiation Effects on Semiconductor Materials, Detectors and Devices



Wednesday 8 October 2014 - Friday 10 October 2014

Firenze, Italy

Scientific Programme

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The scientific program of the Conference will cover many state-of-the-art scientific and technological advances in semiconductor materials, detector systems, electronics for research and applications in the fields of medicine, material science, high energy physics, astrophysics.

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Topics

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Materials science techniques based on radiation probes;

Microscopic Disorder in irradiated semiconductors;

Radiation effects on semiconductor materials (massive, thin films, nanostructures);

Radiation effects on wide-band gap materials;

Radiation hardening technologies;

Tracking performance of silicon devices in HEP experiments;

Detector development for possible upgrade of luminosity at LHC;

Simulation of radiation damage and transport properties;

Non-ionising energy loss modellization;

Applications of semiconductor-based devices in electronics, medical physics, space experiments.